VISHAY MAS
GENERAL SEMICONDUCTOR

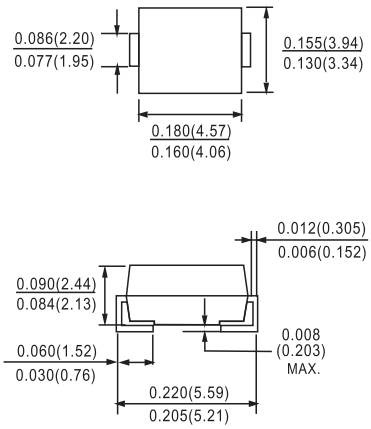
FR2A THRU FR2M

50V-1000V 2.0A

Features

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- Fast switching for high efficiency
- Low reverse leakage
- High forward surge current capability
- For surface mounted applications

DO-214AA(SMB)



Dimensions in inches and (millimeters)

Mechanical Data

- **Case:** Molded plastic, DO-214AA (SMB).
- **Terminals:** Solder plated, solderable per MIL-STD-750, method 2026
- **Polarity:** Color band denotes cathode end

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Ratings at 25℃ ambient temperature unless otherwise specified.
Single phase half-wave 60Hz,resistive or inductive load,for capacitive load current derate by 20%.

	SYMBOLS	FR2A	FR2B	FR2D	FR2G	FR2J	FR2K	FR2M	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at T_L=90℃	$I_{(AV)}$	2.0							Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	50.0							Amps
Maximum instantaneous forward voltage at 2.0A	V_F	1.3							Volts
Maximum DC reverse current T_A=25℃ at rated DC blocking voltage T_A=100℃	I_R	5.0 50.0							uA
Maximum reverse recovery time (NOTE 1)	t_{rr}	150				250	500		ns
Typical junction capacitance (NOTE 2)	C_J	50.0							pF
Typical thermal resistance (NOTE 3)	R_{qJA}	20.0							℃/W
Operating junction and storage temperature range	T_J,T_{STG}	-65 to +150							℃

Note:1.Reverse recovery condition I_F=0.5A,I_R=1.0A,Irr=0.25A
2.Measured at 1MHz and applied reverse voltage of 4.0V D.C.
3.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas